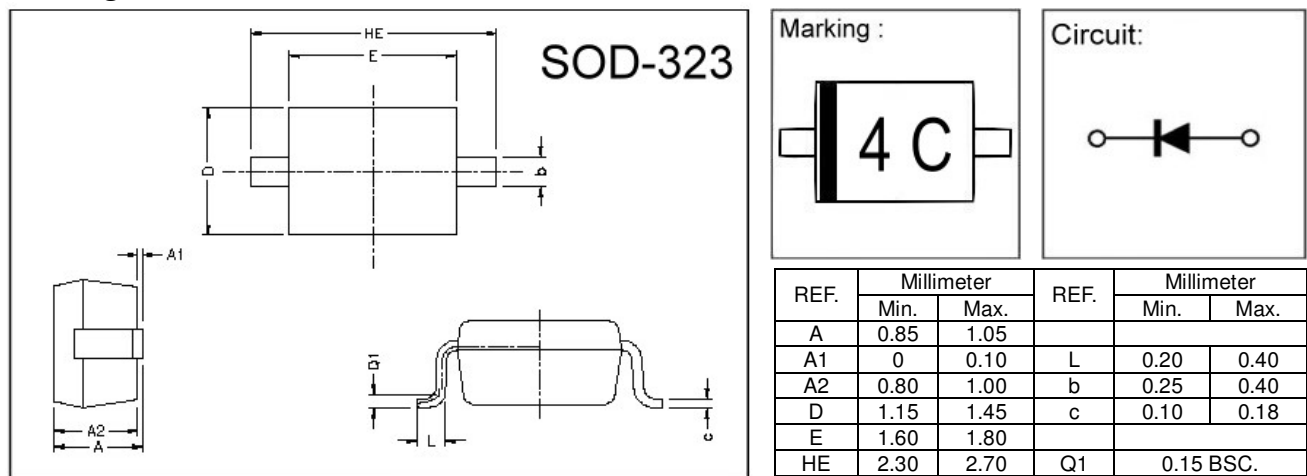


GD1SS356**SURFACE MOUNT, BAND SWITCHING DIODE**
VOLTAGE 35V, CURRENT 0.1A**Description**

The GD1SS356 is designed for high frequency switching application.

Features

- High reliability
- Small mode type

Package Dimensions**Absolute Maximum Ratings at Ta = 25°C**

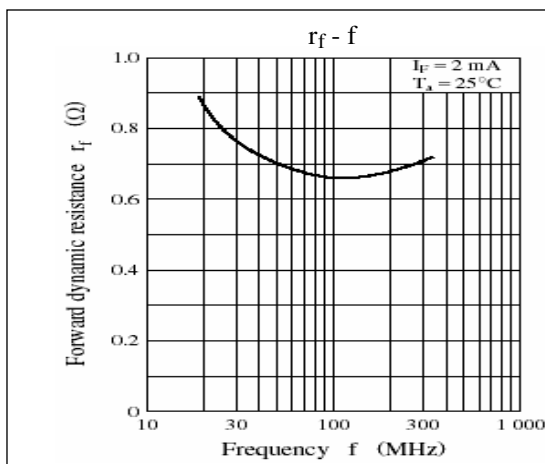
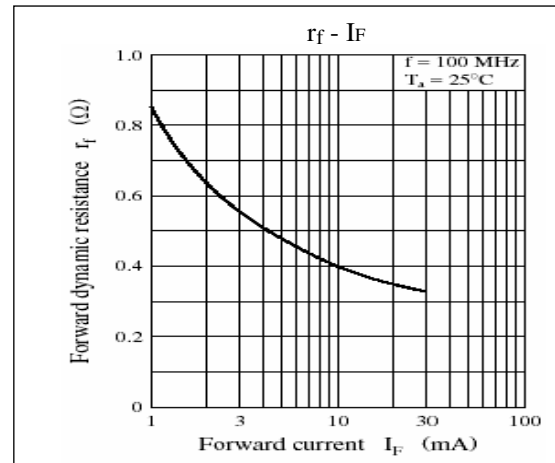
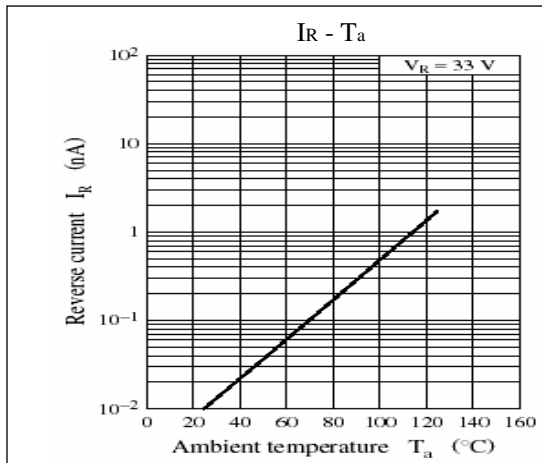
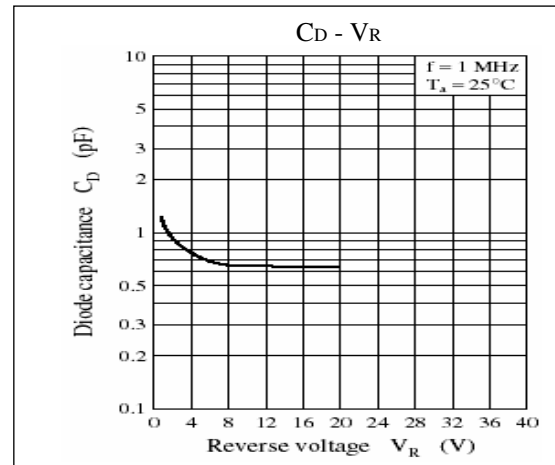
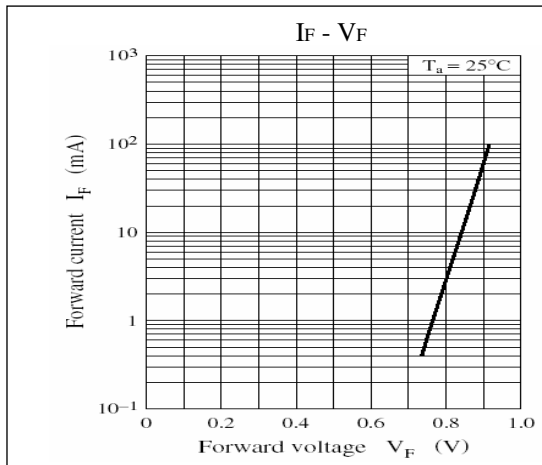
Parameter	Symbol	Ratings	Unit
Reverse Voltage(DC)	V_R	35	V
Forward Current(DC)	I_F	100	mA
Junction Temperature	T_j	+125	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C
Total Power Dissipation	P_D	225	mW

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown	V_R	35	-	-	V	$I_R=10\mu A$
Reverse Current(DC)	I_R	-	-	10	nA	$V_R=25V$
Reverse Voltage(DC)	V_F	-	-	1	V	$I_F=10mA$
Diode Capacitance	C_D	-	0.9	1.2	pF	$V_R=6, f=1MHz$
Forward dynamic resistance	r_f	-	0.65	0.9	Ω	$I_F=2mA, f=100MHz$

Note 1: Rated input/output frequency: 100MHz

Characteristics Curve

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